

2SK1374

Silicon N-channel MOSFET

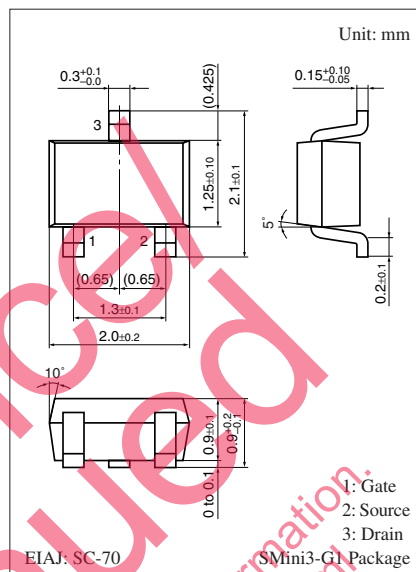
For switching circuits

■ Features

- High-speed switching
- Wide frequency band
- Incorporating a built-in gate protection-diode
- Allowing 2.5 V drive

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-source voltage	V_{DS}	50	V
Gate-source voltage (Drain open)	V_{GSO}	10	V
Drain current	I_D	50	mA
Peak drain current	I_{DP}	100	mA
Power dissipation	P_D	150	mW
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



Marking Symbol: 4V

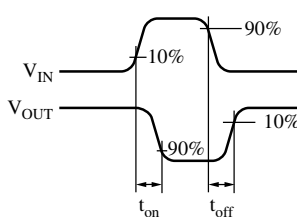
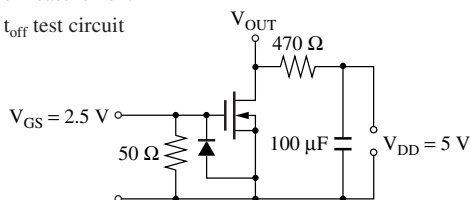
■ Electrical Characteristics $T_a = 25^\circ\text{C}$

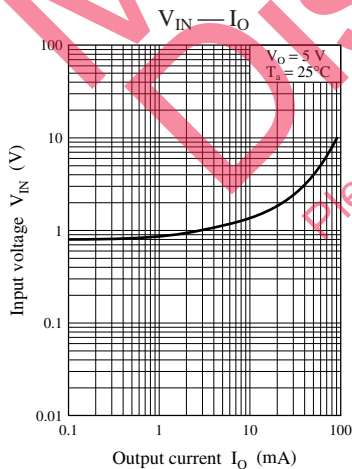
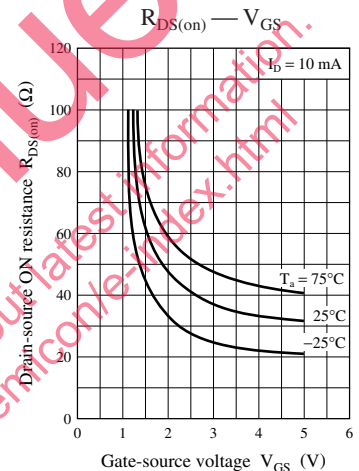
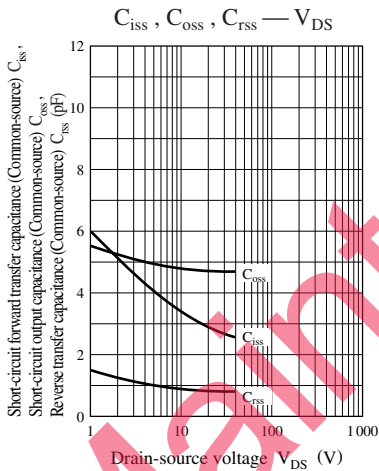
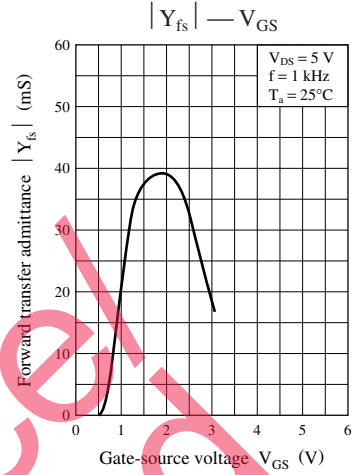
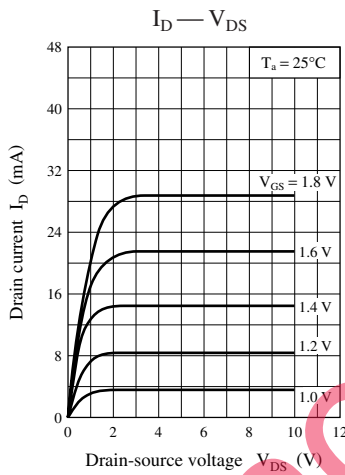
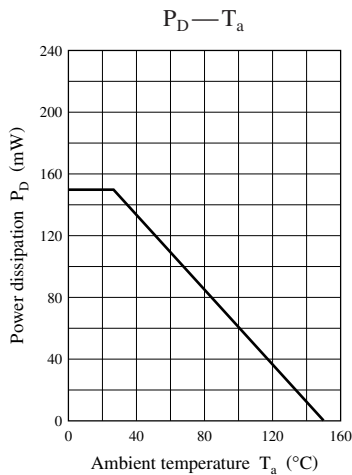
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source surrender voltage	V_{DSS}	$I_D = 10 \mu\text{A}, V_{GS} = 0$	50	100		V
Drain-source cutoff current	I_{DSS}	$V_{DS} = 20 \text{V}, V_{GS} = 0$			1.0	μA
Gate-source cutoff current	I_{GSS}	$V_{GS} = 10 \text{V}, V_{DS} = 0$			1.0	μA
Gate threshold voltage	V_{th}	$I_D = 100 \mu\text{A}, V_{DS} = 5 \text{V}$	0.5	0.8	1.1	V
Forward transfer admittance	$ Y_{fs} $	$I_D = 10 \text{mA}, V_{DS} = 5 \text{V}, f = 1 \text{kHz}$	20	39		mS
Drain-source ON resistance	$R_{DS(on)}$	$I_D = 10 \text{mA}, V_{GS} = 2.5 \text{V}$		27	50	Ω
Short-circuit forward transfer capacitance (Common source)	C_{iss}	$V_{DS} = 5 \text{V}, V_{GS} = 0, f = 1 \text{MHz}$		4.5		pF
Short-circuit output capacitance (Common source)	C_{oss}			4.1		pF
Reverse transfer capacitance (Common source)	C_{rss}			1.2		pF
Turn-on time *1, 2	t_{on}	$V_{DD} = 5 \text{V}, R_L = 470 \Omega, V_{GS} = 0 \text{V to } 2.5 \text{V}$		0.2		μs
Turn-off time *1, 2	t_{off}	$V_{DD} = 5 \text{V}, R_L = 470 \Omega, V_{GS} = 2.5 \text{V to } 0 \text{V}$		0.2		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement

*2: t_{on}, t_{off} test circuit





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